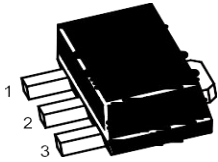


<b>TRANSISTOR(PNP)</b>	<b>SOT-89Plastic-EncapsulateTransistors</b>
<p><u>SOT-89</u></p>  <p>1.Base 2.Collector 3.Emitter SOT-89 Plastic Package</p>	<p><b>Features</b></p> <p>Compliment to SS8050</p>

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

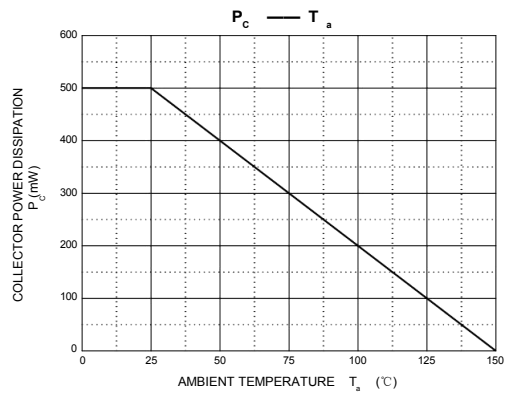
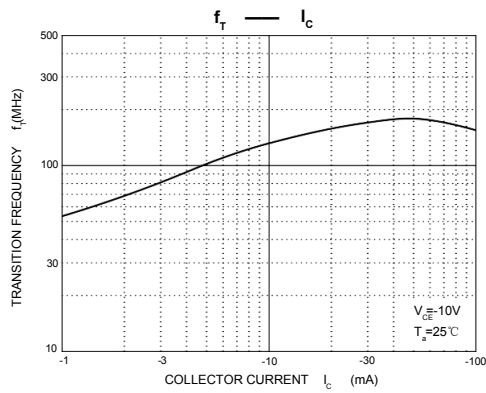
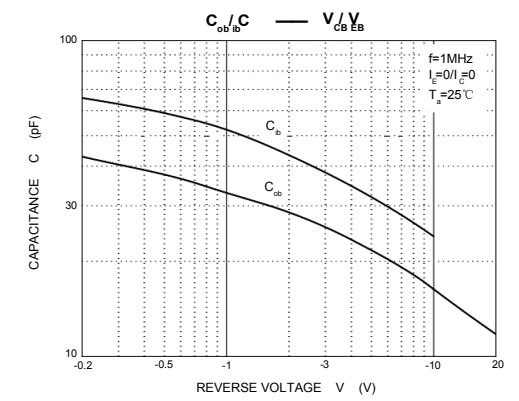
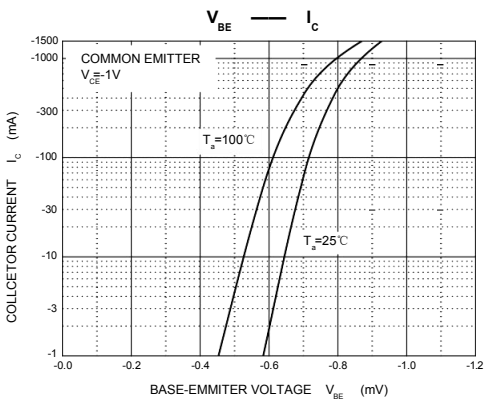
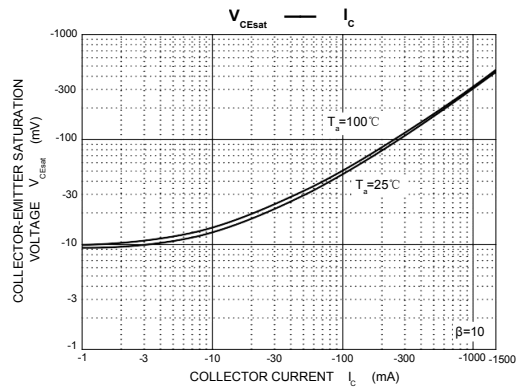
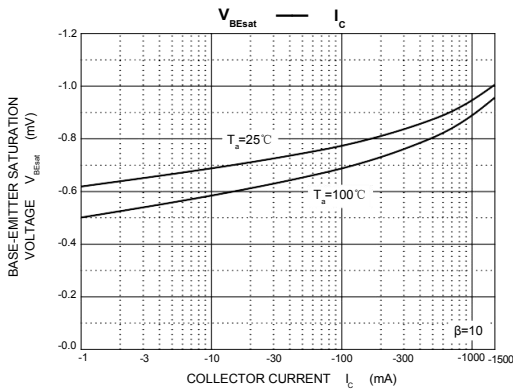
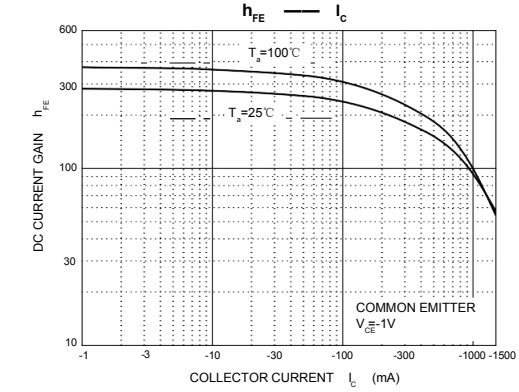
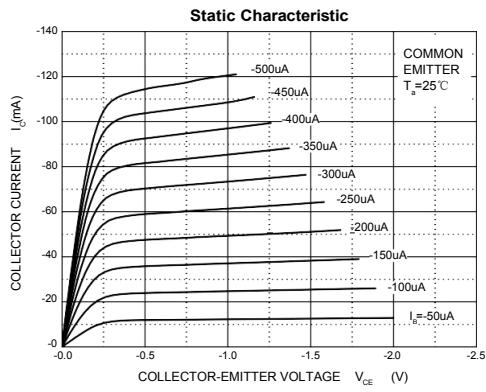
Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>c</sub>	Collector Current -Continuous	-1.5	A
P <sub>c</sub>	Collector Power Dissipation	0.5	W
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	250	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

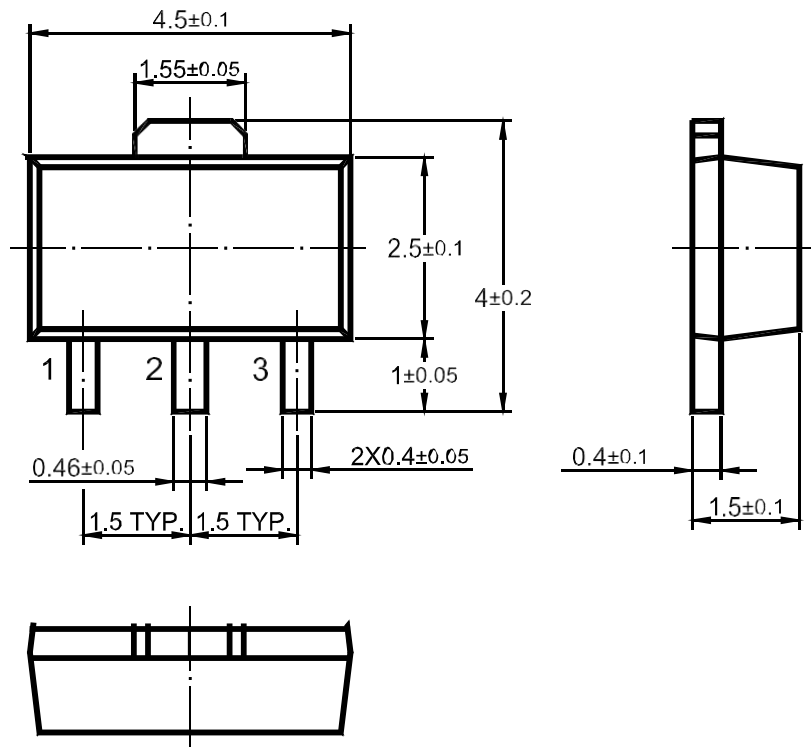
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> = -100μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = -0.1mA, I <sub>B</sub> =0	-25		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -40 V, I <sub>E</sub> =0		-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -20V, I <sub>B</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0		-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	120	400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -800mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> = -80mA		-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> = -80mA		-1.2	V
Base-emitter on voltage	V <sub>BE(on)</sub>	I <sub>C</sub> =-1V, V <sub>CE</sub> =-10mA		-1	V
Base-emitter positive favor voltage	V <sub>BEF</sub>	I <sub>B</sub> =-1A		-1.55	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA	100		MHZ
output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHZ		20	pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	C	D	D1	D2
Range	120-200	160-300	200-350	300-400



**SOT-89 Package Outline Dimensions**



Dimensions in mm

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)